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**ABSTRACT**

An imaging device which has a stacked-layer structure and can be manufactured easily is provided. The imaging device includes a signal processing circuit, a memory device, and an image sensor. The imaging device has a stacked-layer structure in which the memory device is provided above the signal processing circuit, and the image sensor is provided above the memory device. The signal processing circuit includes a transistor formed on a first semiconductor substrate, the memory device includes a transistor including a metal oxide in a channel formation region, and the image sensor includes a transistor formed on a second semiconductor substrate.

